

Fig. 1 is a cross-sectional view of a semiconductor device. It shows a substrate 1 with a layer 1a and a layer 1b. A structure 10 is formed on layer 1b, consisting of layers 10a, 10b, and 10c. A contact 4 is formed on top of layer 10a.

FIG. 4

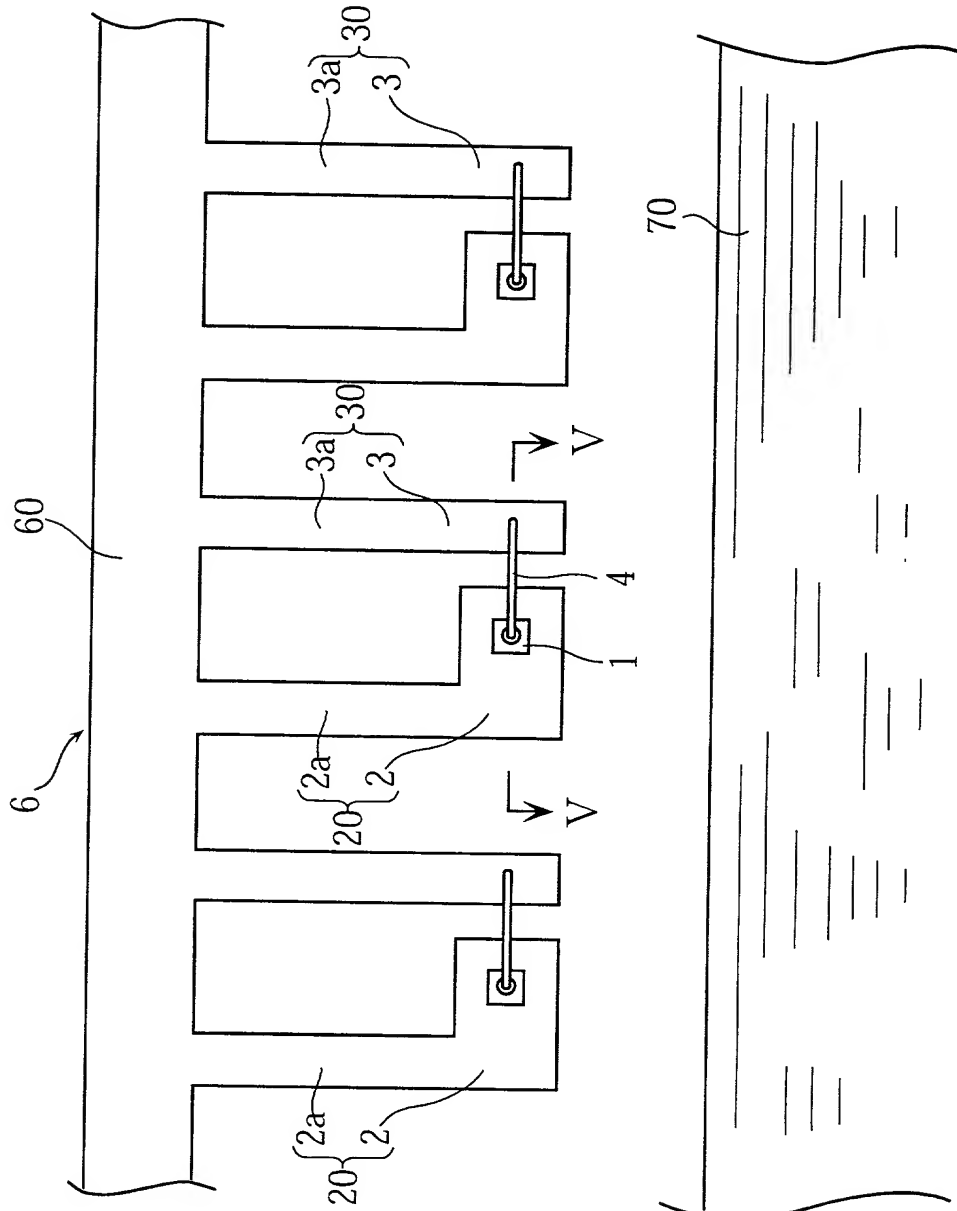


FIG. 5

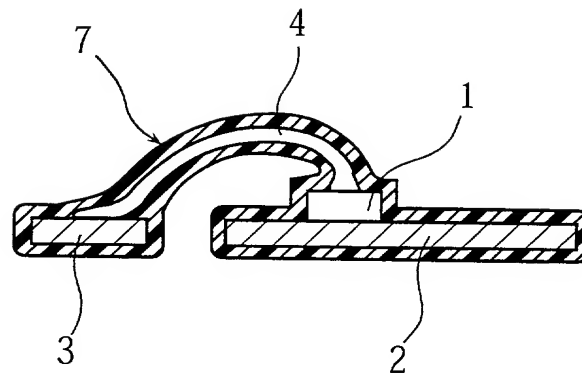


FIG. 6

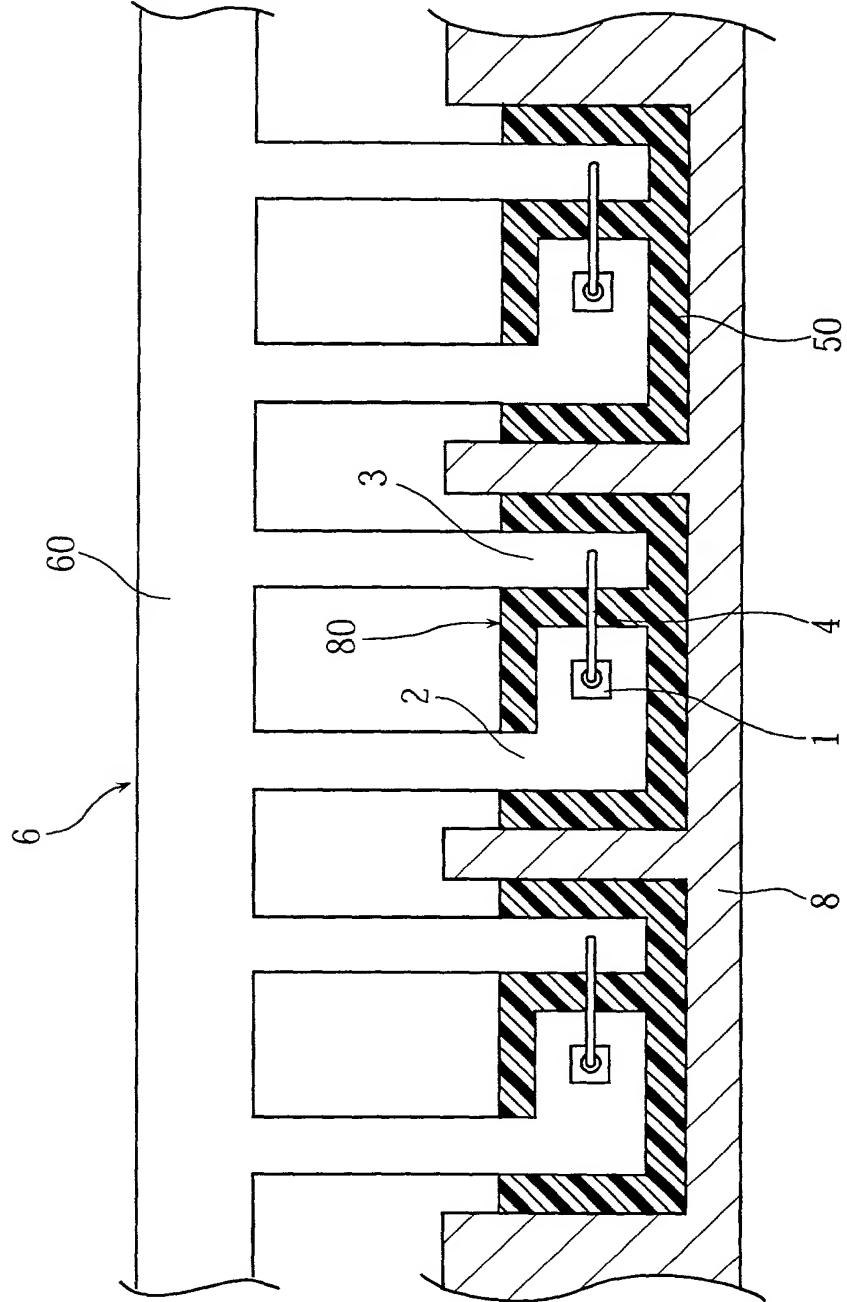


FIG. 7  
PRIOR ART

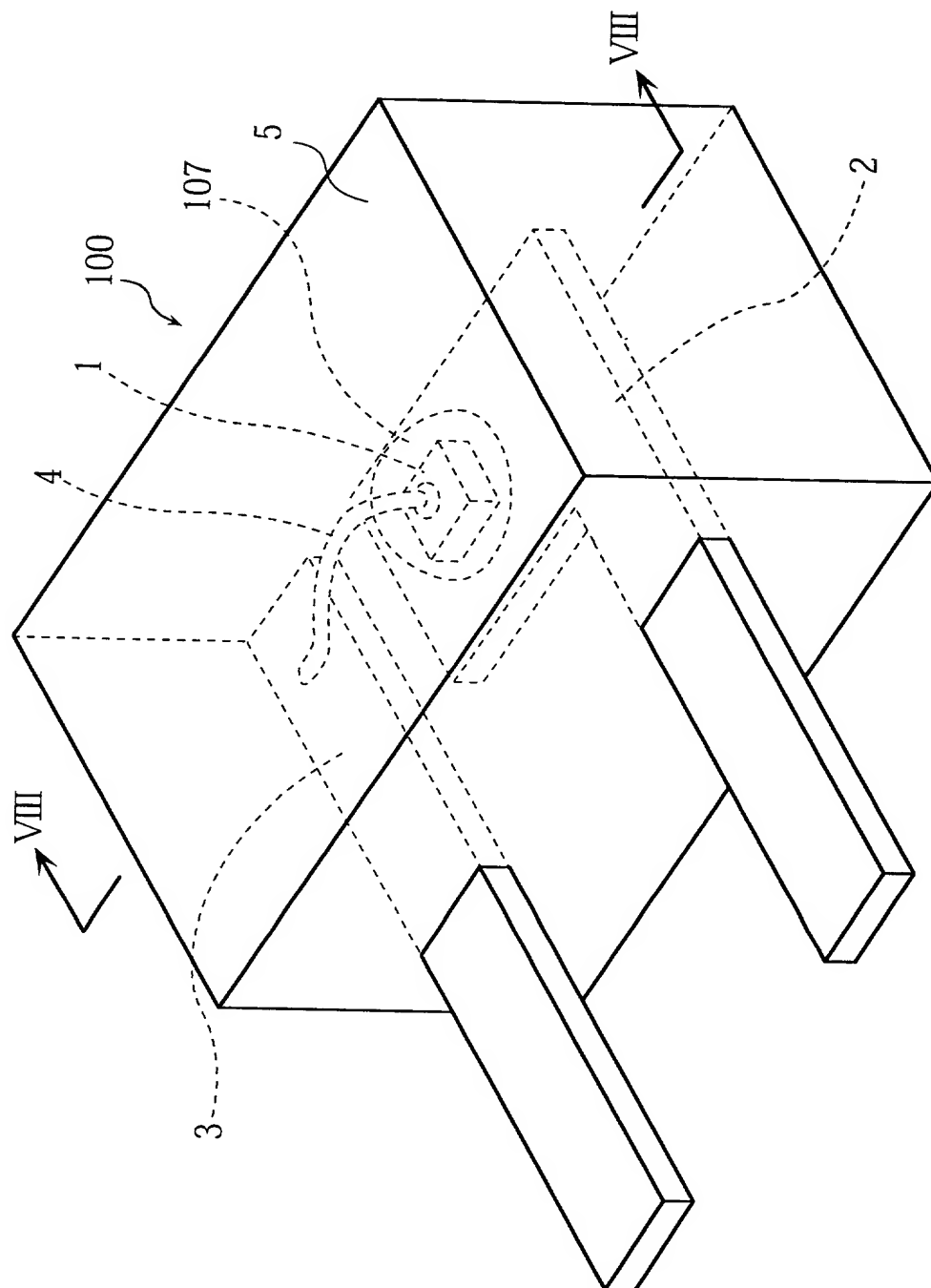


FIG. 8  
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